

PATENT ABSTRACTS OF JAPAN

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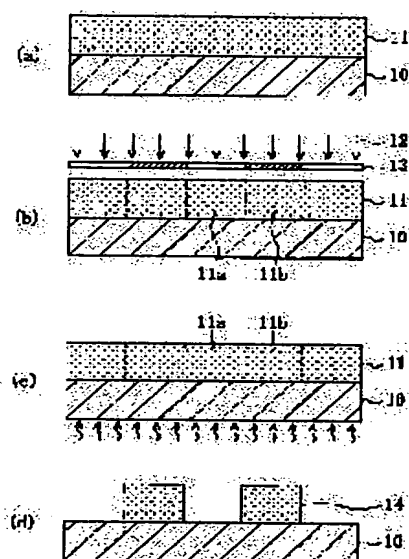
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(54) METHOD OF FORMING PATTERN

(57)Abstract:

PROBLEM TO BE SOLVED: To decrease an edge roughness of lines in a resist pattern obtained by irradiation with electron beams at a low acceleration voltage.

SOLUTION: A resist film 11 consisting of a chemically amplifying resist material having an acid generating agent containing nonafluorobutane sulfonic acid as an anion is formed. The resist film 11 is selectively irradiated with electron beams at a ≤ 10 kV low acceleration voltage for pattern exposure and then developed to form a resist pattern 14.



LEGAL STATUS

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